

# United States Patent and Trademark Office



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO	
10/752,929	01/07/2004	Andrew Marshall	TI-20142.2	5790	
23494 75	90 07/21/2005		EXAMINER		
TEXAS INSTRUMENTS INCORPORATED P O BOX 655474, M/S 3999 DALLAS, TX 75265			LE, TH	LE, THAO X	
			ART UNIT	PAPER NUMBER	
,			2814	2814	
			DATE MAILED: 07/21/2005		

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)			
	10/752,929	MARSHALL ET AL.			
Office Action Summary	Examiner	Art Unit			
	Thao X. Le	2814			
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply					
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period w. Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	6(a). In no event, however, may a reply be tim within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. O (35 U.S.C. § 133).			
Status					
1)⊠ Responsive to communication(s) filed on 13 May 2005.					
	action is non-final.	·			
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims	•				
4) Claim(s) 25-28 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration.  5) □ Claim(s) is/are allowed.  6) □ Claim(s) 25-28 is/are rejected.  7) □ Claim(s) is/are objected to.  8) □ Claim(s) are subject to restriction and/or election requirement.					
Application Papers					
9) The specification is objected to by the Examiner 10) The drawing(s) filed on is/are: a) access applicant may not request that any objection to the of Replacement drawing sheet(s) including the correction of the oath or declaration is objected to by the Examiner	epted or b) objected to by the E drawing(s) be held in abeyance. See on is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d).			
Priority under 35 U.S.C. § 119					
<ul> <li>12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority documents have been received.</li> <li>2. Certified copies of the priority documents have been received in Application No.</li> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>					
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:				

#### **DETAILED ACTION**

### Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.
- 2. Claims 25-26 are rejected under 35 U.S.C. 102(e) as being anticipated by US 6509606 to Merrill et al.

Regarding claim 25, Merrill discloses a method for forming EEPROM cell in fig. 2A-D on a substrate 212, column 6 line 2, having an outer surface, the method comprising the steps of: forming a deep conductive region 220 of a first conductivity type (N-type), column 6 line 7, in the substrate 212 below the substrate's outer surface (top surface of substrate 212); forming first and second conductive regions 214/216, fig. 2C and claim 1, in the substrate 212 below the substrate's outer surface, the first and second conductive regions 214/216 are laterally displaced from one another by a predetermined distance, forming an insulating layer 230, column 6 line 19, outwardly from the outer surface of the substrate 212, fig. 2C, the insulating layer 230 positioned so that its edges are substantially in alignment between the first and second conductive regions 214/216, fig. 2C, forming a floating gate layer 234, column 6 line 29 outwardly from the insulating layer 230 and in substantially the same shape as the insulating layer

Art Unit: 2814

2308, fig. 2C; and wherein the deep conductive region 220 is operable to provide a source of charge for placement on the floating gate layer 234 when programming the EEPROM cell, column 7 lines 58-64.

Regarding claim 26, Chritz discloses the method wherein the insulating layer 230 is formed from oxide, column 6 line 19.

## Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).
- 5. Claims 27-28 are rejected under 35 U.S.C. 103(a) as being unpatentable over US 6509606 to Merrill et al. in view of US 5976956 to Gardner et al or US 6052304 to Chritz

Regarding claim 27, Merrill does not disclose the method wherein the floating gate 234 is formed from polysilicon.

However, Gardner discloses the method wherein the gate 132 is formed from polysilicon, column 10 line 22. Or Chritz discloses the method wherein the gate 310 is formed from polysilicon, column 7 line 20. At the time the invention was made; it would have been obvious to one of ordinary skill in the art to use the polysilicon gate teaching of Gardner or Chritz with Merrill's method, because such polysilicon gate is typical in the art.

Regarding claim 28, Merrill discloses the method wherein the deep conductive region 220 is doped with N having a general doping concentration.

But, Merrill does not disclose the doping concentration on the order of  $1 \times 10^{16} \text{ cm}^{-3}$ .

However, Gardner discloses the method wherein the N deep conductive region having the doping concentration on the order of 1x10<sup>16</sup> cm<sup>-3</sup>, column 4 line 1 or column 7 line 10. Accordingly, it would have been obvious to one of ordinary skill in art to combine N deep doping teaching of Gardner with Chritz in the range as claimed, because it has been held that where the general conditions of the claims are discloses in the prior art, it is not inventive to discover the optimum or workable range by routine experimentation. See In re Aller, 220 F.2d 454, 105 USPQ 233, 235 (CCPA 1955).

### Response to Arguments

6. Applicant's arguments with respect to claims 25-28 on 13 May 2005 have been considered but are most in view of the new ground(s) of rejection.

#### Conclusion

7. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thao X. Le whose telephone number is (571) 272-1708. The examiner can normally be reached on M-F from 8:00 AM - 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Wael M. Fahmy can be reached on (571) 272 -1705. The fax phone

Art Unit: 2814

number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Thao X. Le 12 July 2005

> LONG PHAM PRIMARY EXAMINER